

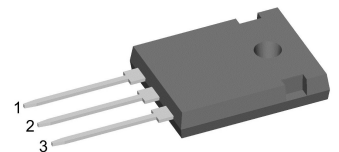
Schottky Diode

$$\begin{aligned} V_{RRM} &= 200 \text{ V} \\ I_{FAV} &= 2 \times 45 \text{ A} \\ V_F &= 0.79 \text{ V} \end{aligned}$$

High Performance Schottky Diode
 Low Loss and Soft Recovery
 Common Cathode

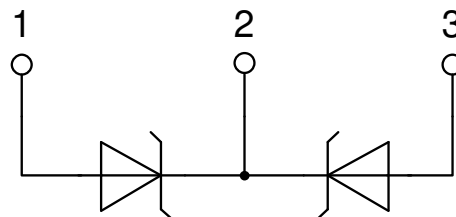
Part number

DSA90C200HR



Backside: isolated

 E72873



Features / Advantages:

- Very low V_f
- Extremely low switching losses
- Low I_{rm} values
- Improved thermal behaviour
- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching

Applications:

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

Package: ISO247

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Soldering pins for PCB mounting
- Backside: DCB ceramic
- Reduced weight
- Advanced power cycling

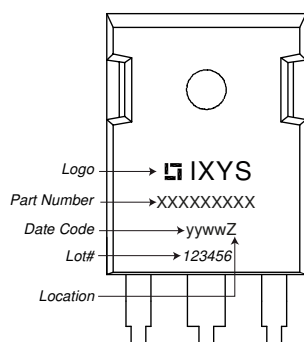
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Schottky				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V _{RSM}	max. non-repetitive reverse blocking voltage	T _{VJ} = 25°C				200	V
V _{RRM}	max. repetitive reverse blocking voltage	T _{VJ} = 25°C				200	V
I _R	reverse current, drain current	V _R = 200 V	T _{VJ} = 25°C			2	mA
		V _R = 200 V	T _{VJ} = 125°C			5	mA
V _F	forward voltage drop	I _F = 45 A	T _{VJ} = 25°C			0.91	V
		I _F = 90 A				1.10	V
		I _F = 45 A	T _{VJ} = 125°C			0.79	V
		I _F = 90 A				1.03	V
I _{FAV}	average forward current	T _C = 145°C rectangular d = 0.5	T _{VJ} = 175°C			45	A
V _{F0}	threshold voltage	} for power loss calculation only				0.49	V
r _F	slope resistance					5.5	mΩ
R _{thJC}	thermal resistance junction to case					0.7	K/W
R _{thCH}	thermal resistance case to heatsink				0.25		K/W
P _{tot}	total power dissipation	T _C = 25°C				215	W
I _{FSM}	max. forward surge current	t = 10 ms; (50 Hz), sine; V _R = 0 V		T _{VJ} = 45°C		600	A
C _J	junction capacitance	V _R = 24 V f = 1 MHz		T _{VJ} = 25°C		394	pF

Package ISO247			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal ¹⁾			70	A
T_{VJ}	virtual junction temperature		-55		175	°C
T_{op}	operation temperature		-55		150	°C
T_{stg}	storage temperature		-55		150	°C
Weight				6		g
M_D	mounting torque		0.8		1.2	Nm
F_C	mounting force with clip		20		120	N
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	2.7			mm
$d_{Spb/Apb}$		terminal to backside	4.1			mm
V_{ISOL}	isolation voltage	t = 1 second	3600			V
		t = 1 minute	3000			V

Product Marking



Part description

D = Diode
 S = Schottky Diode
 A = low VF
 90 = Current Rating [A]
 C = Common Cathode
 200 = Reverse Voltage [V]
 HR = ISO247 (3)

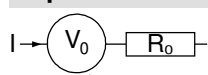
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSA90C200HR	DSA90C200HR	Tube	30	508368

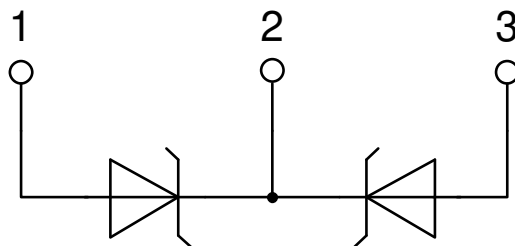
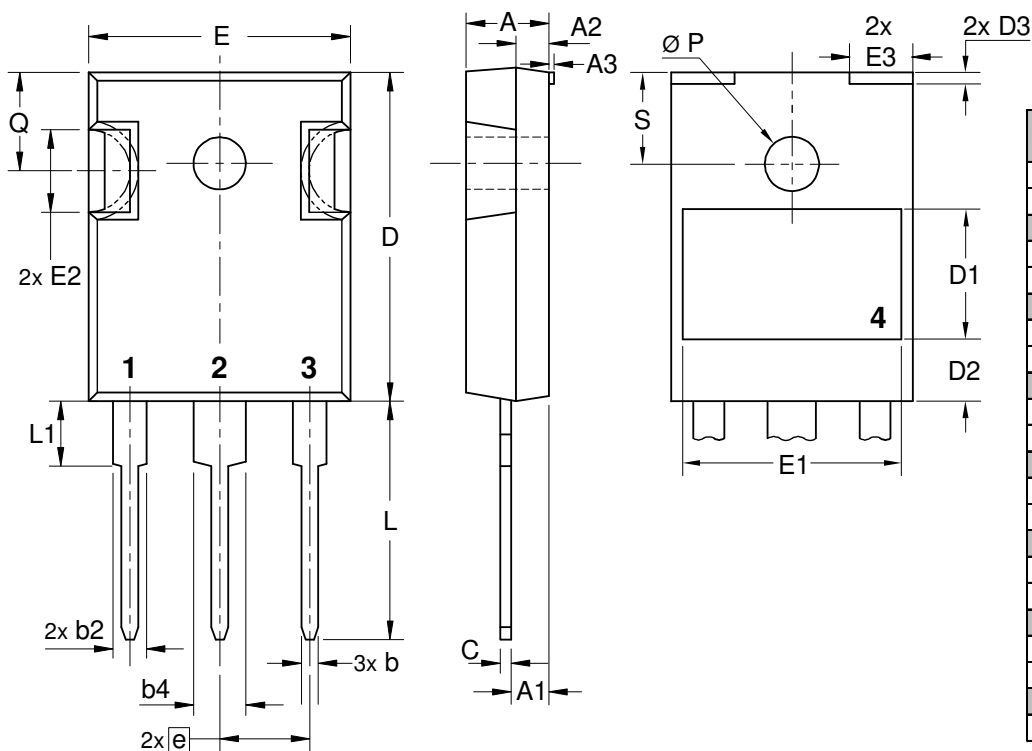
Similar Part	Package	Voltage class
DSSK60-02AR	ISOPLUS247 (3)	200
DSSK60-02A	TO-247AD (3)	200

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 175^{\circ}\text{C}$

		Schottky	
$V_{0\ max}$	threshold voltage	0.49	V
$R_{0\ max}$	slope resistance *	2.9	mΩ

Outlines ISO247


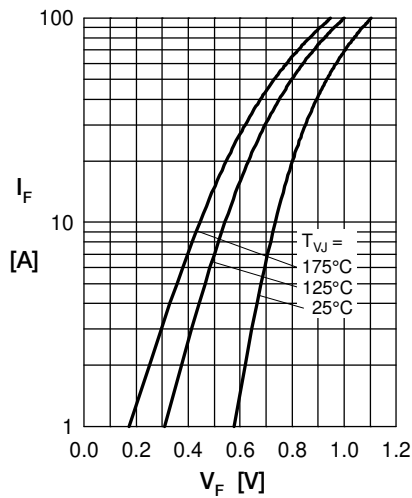
Schottky


Fig. 1 Max. forward voltage drop characteristics

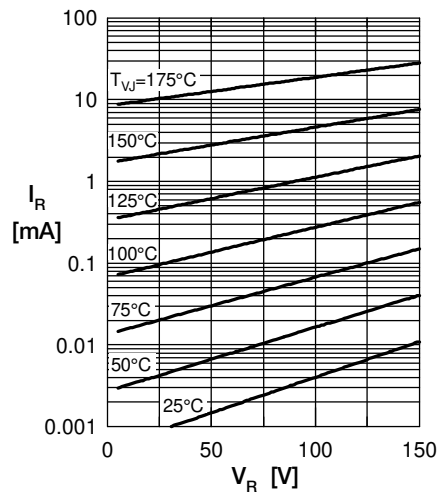


Fig. 2 Typ. reverse current I_R vs. reverse voltage V_R

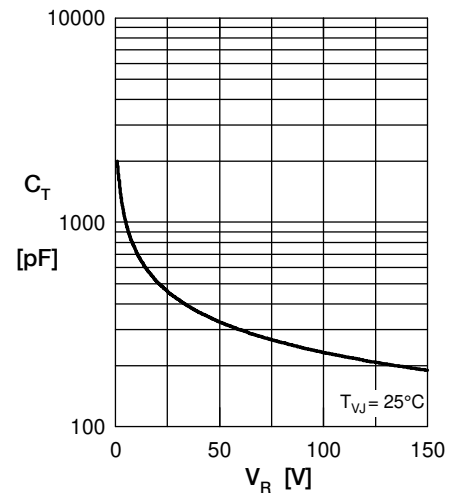


Fig. 3 Typ. junction capacitance C_T vs. reverse voltage V_R

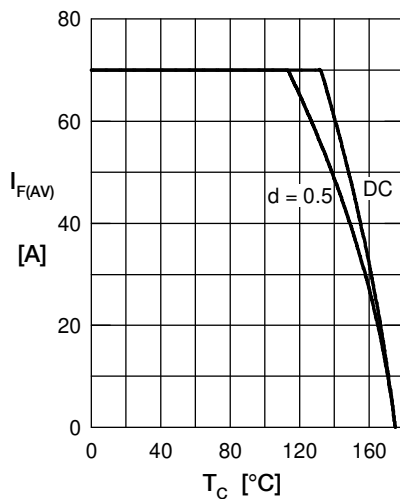


Fig. 4 Avg. forward current $I_{F(AV)}$ vs. case temp. T_C

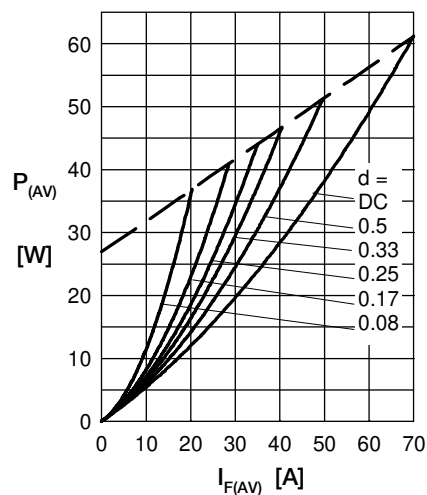


Fig. 5 Forward power loss characteristics

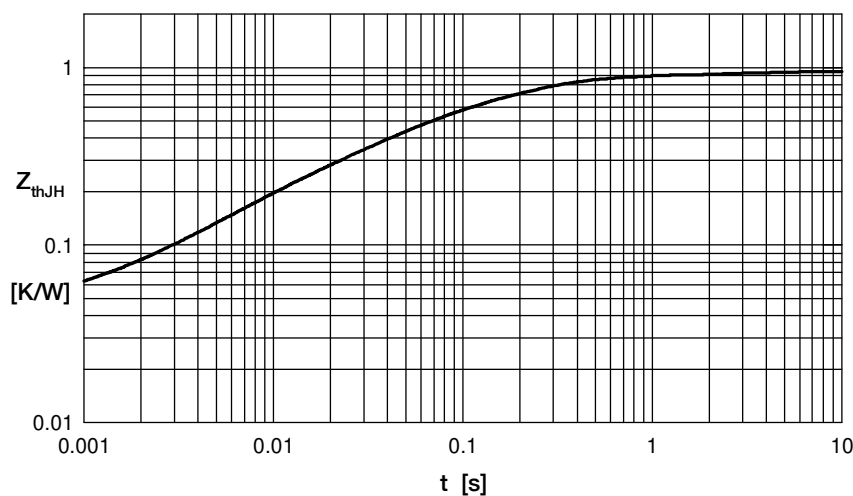


Fig. 6 Transient thermal impedance junction to heatsink

R_{thi}	t_i
0.041	0.0002
0.087	0.0065
0.258	0.037
0.486	0.182
0.078	2.43

Note: All curves are per diode